# SONY

ICX205AL

Diagonal 8mm (Type 1/2) Progressive Scan CCD Image Sensor with Square Pixel for B/W Cameras

#### Description

The ICX205AL is a diagonal 8mm (Type 1/2) interline CCD solid-state image sensor with a square pixel array and 1.45M effective pixels. Progressive scan allows all pixels' signals to be output independently within approximately 1/7.5 second. Also, the adoption of high frame rate readout mode supports 30 frames per second. This chip features an electronic shutter with variable charge-storage time which makes it possible to realize full-frame still image without a mechanical shutter. High sensitivity and low dark current are achieved through the adoption of HAD (Hole-Accumulation Diode) sensors.

This chip is suitable for applications such as electronic still cameras, PC input cameras, etc.

#### Features

- Progressive scan allows individual readout of the image signals from all pixels.
- High horizontal and vertical resolution (both approx. 1024TV-lines) still image without a mechanical shutter.
- Supports high frame rate readout mode (effective 256 lines output, 30 frame/s)
- Square pixel
- Horizontal drive frequency: 14.318MHz
- No voltage adjustments
- (reset gate and substrate bias are not adjusted.)High resolution, high sensitivity, low dark current
- Low smear, excellent antiblooming characteristics
- Continuous variable-speed shutter

#### **Device Structure**

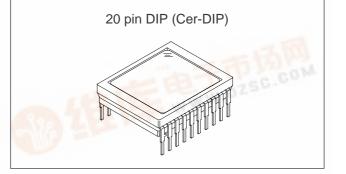
- Interline CCD image sensor
- Image size:
- Total number of pixels:
- Number of effective pixels:
- Number of active pixels:
- Chip size:
- Unit cell size:
- Optical black:
- Number of dummy bits:
- Substrate material:

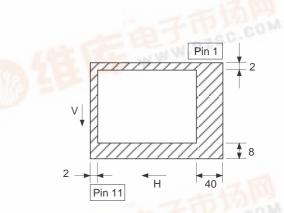
1434 (H) × 1050 (V) approx. 1.50M pixels 1392 (H) × 1040 (V) approx. 1.45M pixels 1360 (H) × 1024 (V) approx. 1.40M pixels (7.959mm diagonal) 7.60mm (H) × 6.20mm (V) 4.65 $\mu$ m (H) × 4.65 $\mu$ m (V) Horizontal (H) direction: Front 2 pixels, rear 40 pixels Vertical (V) direction: Front 8 pixels, rear 2 pixels Horizontal 20 Vertical 3 Silicon

Sony reserves the right to change products and specifications without prior notice. This information does not convey any license by any implication or otherwise under any patents or other right. Application circuits shown, if any, are typical examples illustrating the operation of the devices. Sony cannot assume responsibility for any problems arising out of the use of these circuits.

Diagonal 8mm (Type 1/2)



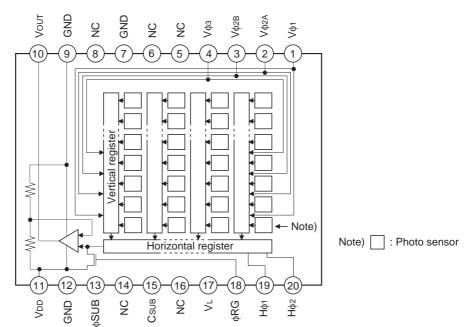






# **Block Diagram and Pin Configuration**

(Top View)



# **Pin Description**

Pin No.	Symbol	Description	Pin No.	Symbol	Description
1	Vφ1	Vertical register transfer clock	11	Vdd	Supply voltage
2	Vφ2Α	Vertical register transfer clock	12	GND	GND
3	Vф2в	Vertical register transfer clock	13	φSUB	Substrate clock
4	Vфз	Vertical register transfer clock	14	NC	
5	NC		15	Сѕив	Substrate bias*1
6	NC		16	NC	
7	GND	GND	17	VL	Protective transistor bias
8	NC		18	φRG	Reset gate clock
9	GND	GND	19	Ηφ1	Horizontal register transfer clock
10	Vout	Signal output	20	Ηφ2	Horizontal register transfer clock

\*1 DC bias is generated within the CCD, so that this pin should be grounded externally through a capacitance of 0.1µF.

# **Absolute Maximum Ratings**

	Item	Ratings	Unit	Remarks
	Vdd, Vout, $\phi RG - \phi SUB$	JB   -40 to +10   V     -50 to +15   V     -50 to +0.3   V     -50 to +0.3   V     -50 to +0.3   V     -40 to +0.3   V     -25 to   V     -25 to   V     -0.3 to +18   V     -GND   -10 to +18   V     -10 to +15   V     -0.3 to +28   V     ND - VL   -0.3 to +15   V		
	Vφ2Α, Vφ2Β – φSUB	–50 to +15	V	
Against	$V\phi_1, V\phi_3, V_L - \phi SUB$	-50 to +15     -50 to +0.3     B   -40 to +0.3     -25 to     -GND   -0.3 to +18     GND   -10 to +18     -10 to +15   -0.3 to +28	V	
	Hφ1, Hφ2, GND – φSUB	-40 to +0.3	V	
	Csub – фSUB	–25 to	-50 to +15 V   -50 to +0.3 V   -40 to +0.3 V   -25 to V   -0.3 to +18 V   -10 to +18 V   -10 to +15 V   -0.3 to +28 V   -0.3 to +15 V	
	VDD, VOUT, $\phi$ RG, CSUB – GND	-0.3 to +18	V	
Against GND	Vφ1, Vφ2Α, Vφ2Β, Vφ3 – GND	-10 to +18	V	
	Hφ1, Hφ2 – GND	-10 to +15	V	
Against \/	Vq2a, Vq2b – Vl	-0.3 to +28	V	
Against V∟	Vφ1, Vφ3, Hφ1, Hφ2, GND – VL	-0.3 to +15	V	
_	Voltage difference between vertical clock input pins	to +15	V	*1
Between input clock pins	Ηφ1 – Ηφ2	-16 to +16	V	
	Ηφ1, Ηφ2 – Vφ3	-16 to +16	V	
Storage temper	ature	-30 to +80	°C	
Operating temp	erature	-10 to +60	°C	

 $^{*1}$  +24V (Max.) when clock width < 10µs, clock duty factor < 0.1%.

+16V (Max.) is guaranteed for turning on or off power supply.

# **Bias Conditions**

Item	Symbol	Min.	Тур.	Max.	Unit	Remarks
Supply voltage	Vdd	14.55	15.0	15.45	V	
Protective transistor bias	VL		*1			
Substrate clock	φSUB		*2			
Reset gate clock	φRG		*2			

\*1 VL setting is the VvL voltage of the vertical transfer clock waveform, or the same power supply as the VL power supply for the V driver should be used.

\*2 Do not apply a DC bias to the substrate clock and reset gate clock pins, because a DC bias is generated within the CCD.

# **DC Characteristics**

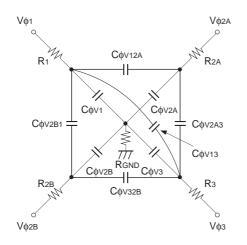
Item	Symbol	Min.	Тур.	Max.	Unit	Remarks
Supply current	Idd		5.5		mA	

# **Clock Voltage Conditions**

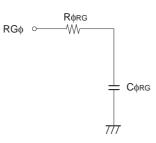
Item	Symbol	Min.	Тур.	Max.	Unit	Waveform diagram	Remarks
Readout clock voltage	Vvт	14.55	15.0	15.45	V	1	
	Vvh02a	-0.05	0	0.05	V	2	Vvh = Vvh02a
Vertical transfer clock voltage	Vvh1, Vvh2a, Vvh2b, Vvh3	-0.2	0	0.05	V	2	
	Vvl1, Vvl2a, Vvl2b, Vvl3	-8.4	-8.0	-7.6	V	2	Vvl = (Vvl1 + Vvl3)/2
	Vφ1, Vφ2Α, Vφ2Β, Vφ3	7.6	8.0	8.4	V	2	
	Vvl1 – Vvl3			0.1	V	2	
	Vvнн			0.9	V	2	High-level coupling
	Vvhl			1.3	V	2	High-level coupling
	Vvlh			1.0	V	2	Low-level coupling
	Vvll			0.9	V	2	Low-level coupling
Horizontal transfer	Vфн	4.75	5.0	5.25	V	3	
clock voltage	Vhl	-0.05	0	0.05	V	3	
	Vørg	3.0	3.3	5.5	V	4	
Reset gate clock voltage	Vrglh – Vrgll			0.4	V	4	Low-level coupling
	Vrgl – Vrglm			0.5	V	4	Low-level coupling
Substrate clock voltage	Vфsuв	22.15	23.0	23.85	V	5	

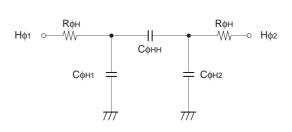
# **Clock Equivalent Circuit Constant**

Item	Symbol	Min.	Тур.	Max.	Unit	Remarks
	<b>C</b> φv1		2200		pF	
Capacitance between vertical transfer clock and	<b>C</b> φν2A		1800		pF	
Capacitance between vertical transfer clock and GND Capacitance between vertical transfer clocks Capacitance between horizontal transfer clock and GND Capacitance between horizontal transfer clocks Capacitance between reset gate clock and GND Capacitance between reset gate clock and GND Capacitance between substrate clock and GND	Сфv2в		6800		pF	
	Сф∨з		3300		pF pF	
	Сфv12А, Сфv2В1		1200		pF	
Capacitance between vertical transfer clocks	Сфигаз, Сфизгв		1200		pF	
	Сфv13		2200		pF	
Capacitance between horizontal transfer clock and GND	Сфн1, Сфн2		47		pF	
Capacitance between horizontal transfer clocks	Сфнн		100		pF	
Capacitance between reset gate clock and GND	Cộrg		8		pF	
Capacitance between substrate clock and GND	Сфѕив		680		pF	
	R1		36		Ω	
Vertical transfer clock series resistor	R2A, R3		56		Ω	
	R <sub>2B</sub>		43		Ω	
Vertical transfer clock ground resistor	Rgnd		30		Ω	
Horizontal transfer clock series resistor	Rфн		15		Ω	
Reset gate clock series resistor	Rørg		20		Ω	



# Vertical transfer clock equivalent circuit



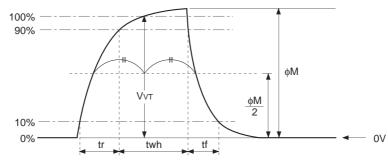


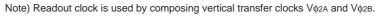
# Horizontal transfer clock equivalent circuit

#### **Drive Clock Waveform Conditions**

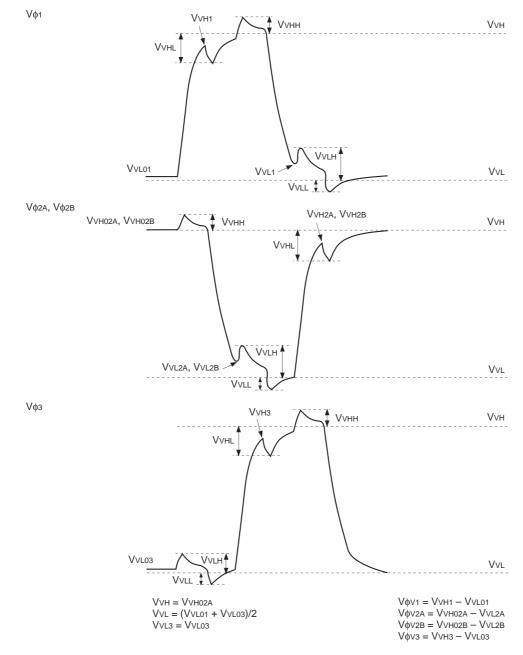
#### (1) Readout clock waveform

Vт

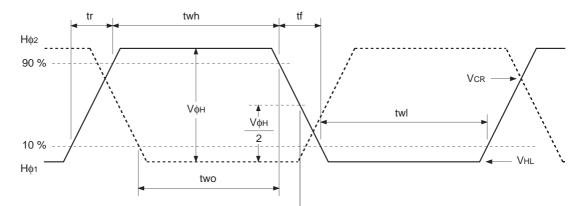




#### (2) Vertical transfer clock waveform

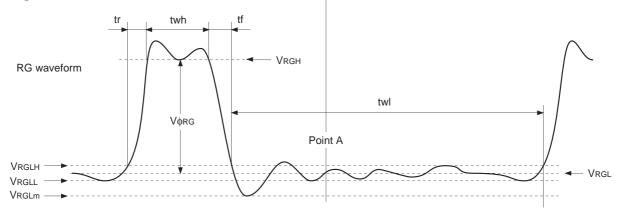


#### (3) Horizontal transfer clock waveform



Cross-point voltage for the H $\phi_1$  rising side of the horizontal transfer clocks H $\phi_1$  and H $\phi_2$  waveforms is Vcr. The overlap period for twh and twl of horizontal transfer clocks H $\phi_1$  and H $\phi_2$  is two.

#### (4) Reset gate clock waveform



VRGLH is the maximum value and VRGLL is the minimum value of the coupling waveform during the period from Point A in the above diagram until the rising edge of RG.

In addition, VRGL is the average value of VRGLH and VRGLL.

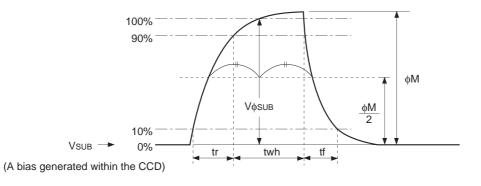
VRGL = (VRGLH + VRGLL)/2

Assuming VRGH is the minimum value during the interval twh, then:

 $V\phi RG = VRGH - VRGL.$ 

Negative overshoot level during the falling edge of RG is VRGLm.

#### (5) Substrate clock waveform



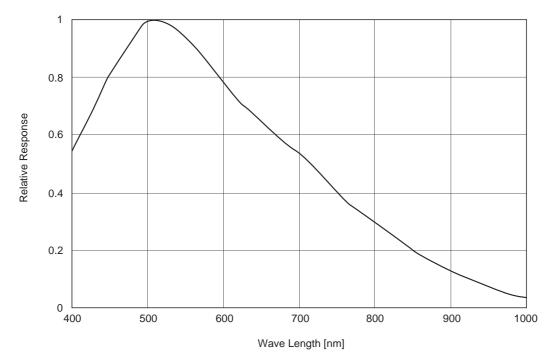
# **Clock Switching Characteristics**

	Item	Symbol		twh			twl			tr			tf		Unit	Remarks
nem		Symbol	Min.	Тур.	Max.	Unit	Remarks									
Rea	dout clock	Vт	2.3	2.5						0.5			0.5		μs	During readout
Ver cloc	tical transfer k	Vφ1, Vφ2A, Vφ2B, Vφ3										15		450	ns	*1
ck	During imaging	Hφ1	20	25		20	25			10	15		10	15	ns	*2
Horizontal transfer clock		Hø2	20	25		20	25			10	15		10	15		-
Horizontal transfer cl	During	Hφ1								0.01			0.01			
Ho tra	parallel-serial conversion	Hø2								0.01			0.01		- µs	
Res	et gate clock	φRG	11	13			51			3			3		ns	
Sub	strate clock	фѕив		2.2							0.5			0.5	μs	During drain charge

 $^{*1}\,$  When vertical transfer clock driver CXD1267AN  $\times\,2$  is used.

ltem	Symbol	two			Unit	Remarks	
ltem	Cymbol	Min.	Тур.	Max.		ITEIIIdIK5	
Horizontal transfer clock	Ηφ1, Ηφ2	16	20		ns		

# Spectral Sensitivity Characteristics (excludes lens characteristics and light source characteristics)

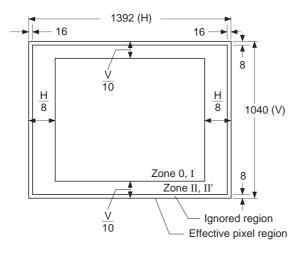


#### - 8 -

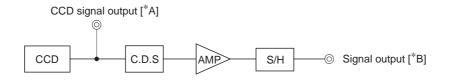
# **Image Sensor Characteristics**

Image Sensor Characteris	nage Sensor Characteristics(Ta = 25°C)									
ltem	Symbol	Min.	Тур.	Max.	Unit	Measurement method	Remarks			
Sensitivity	S	360	450		mV	1	1/30s accumulation			
Saturation signal	Vsat	450			mV	2	Ta = 60°C			
Smear	Sm		0.001	0.0025	%	3	No electronic shutter			
Video signal shading	SH			20	%	4	Zone 0 and I			
video signai shadiriy	511			25	%	4	Zone 0 to II'			
Dark signal	Vdt			16	mV	5	Ta = 60°C			
Dark signal shading	ΔVdt			4	mV	6	Ta = 60°C			
Lag	Lag			0.5	%	7				

#### Zone Definition of Video Signal Shading



#### **Measurement System**

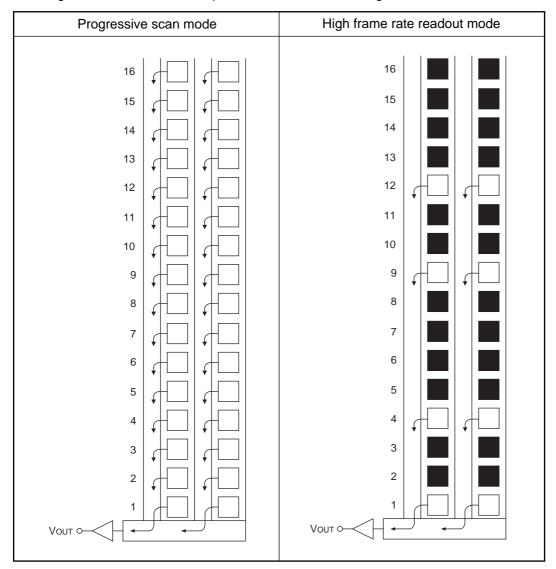


Note) Adjust the amplifier gain so that the gain between [\*A] and [\*B] equals 1.

# Image Sensor Characteristics Measurement Method

### ◎ Readout modes

The diagram below shows the output methods for the following two readout modes.



**Note)** Blacked out portions in the diagram indicate pixels which are not read out. Output starts from the line 1 in high frame rate readout mode.

# 1. Progressive scan mode

In this mode, all pixel signals are output in non-interlace format in 1/7.5s. The vertical resolution is approximately 1024TV-lines and all pixel signals within the same exposure period are read out simultaneously, making this mode suitable for high resolution image capturing.

# 2. High frame rate readout mode

All effective areas are scanned in approximately 1/30s by reading out two out of eight lines (1st and 4th lines, 9th and 12th lines). The vertical resolution is approximately 256TV-lines. This readout mode emphasizes processing speed over vertical resolution.

#### ◎ Measurement conditions

- 1) In the following measurements, the device drive conditions are at the typical values of the progressive scan mode, bias and clock voltage conditions.
- 2) In the following measurements, spot blemishes are excluded and, unless otherwise specified, the optical black level (OB) is used as the reference for the signal output, which is taken as the value measured at point [\*B] of the measurement system.

#### O Definition of standard imaging conditions

1) Standard imaging condition I:

Use a pattern box (luminance : 706cd/m<sup>2</sup>, color temperature of 3200K halogen source) as a subject. (pattern for evaluation is not applicable.) Use a testing standard lens with CM500S (t = 1.0mm) as an IR cut filter and image at F8. The luminous intensity to the sensor receiving surface at this point is defined as the standard sensitivity testing luminous intensity.

2) Standard imaging condition II:

Image a light source (color temperature of 3200K) with a uniformity of brightness within 2% at all angles. Use a testing standard lens with CM500S (t = 1.0mm) as an IR cut filter. The luminous intensity is adjusted to the value indicated in each testing item by the lens diaphragm.

1. Sensitivity

Set to standard imaging condition I. After selecting the electronic shutter mode with a shutter speed of 1/250s, measure the signal output (Vs) at the center of the screen, and substitute the value into the following formula.

$$S = Vs \times \frac{250}{30} [mV]$$

2. Saturation signal

Set to standard imaging condition II. After adjusting the luminous intensity to 10 times the intensity with the average value of the signal output, 150mV, measure the minimum value of the signal output.

3. Smear

Set to standard imaging condition II. With the lens diaphragm at F5.6 to F8, first adjust the luminous intensity to 500 times the intensity with the average value of the signal output, 150mV. Then after the readout clock is stopped and the charge drain is executed by the electronic shutter at the respective H blankings, measure the maximum value (Vsm [mV]) of the signal output and substitute the value into the following formula.

 $Sm = \frac{Vsm}{150} \times \frac{1}{500} \times \frac{1}{10} \times 100 \text{ [\%] (1/10V method conversion value)}$ 

4. Video signal shading

Set to standard imaging condition II. With the lens diaphragm at F5.6 to F8, adjust the luminous intensity so that the average value of the signal output is 150mV. Then measure the maximum (Vmax [mV]) and minimum (Vmin [mV]) values of the signal output and substitute the values into the following formula.

 $SH = (Vmax - Vmin)/150 \times 100 [\%]$ 

5. Dark signal

Measure the average value of the signal output (Vdt [mV]) with the device ambient temperature 60°C and the device in the light-obstructed state, using the horizontal idle transfer level as a reference.

6. Dark signal shading

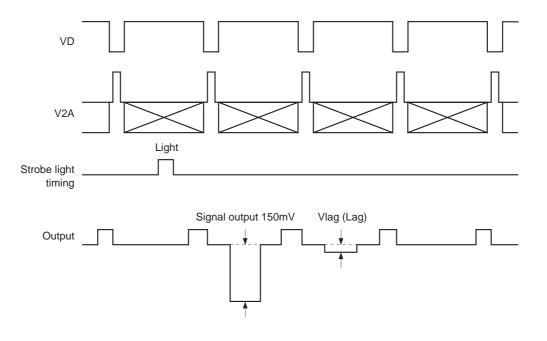
After measuring 5, measure the maximum (Vdmax [mV]) and minimum (Vdmin [mV]) values of the dark signal output and substitute the values into the following formula.

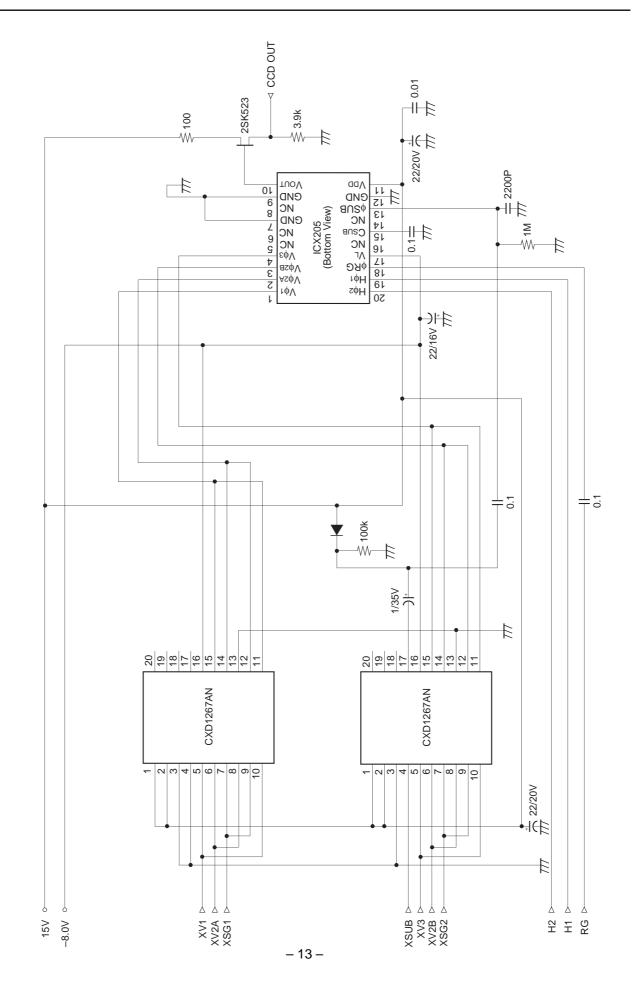
 $\Delta V dt = V dmax - V dmin [mV]$ 

# 7. Lag

Adjust the signal output value generated by strobe light to 150mV. After setting the strobe light so that it strobes with the following timing, measure the residual signal (Vlag). Substitute the value into the following formula.

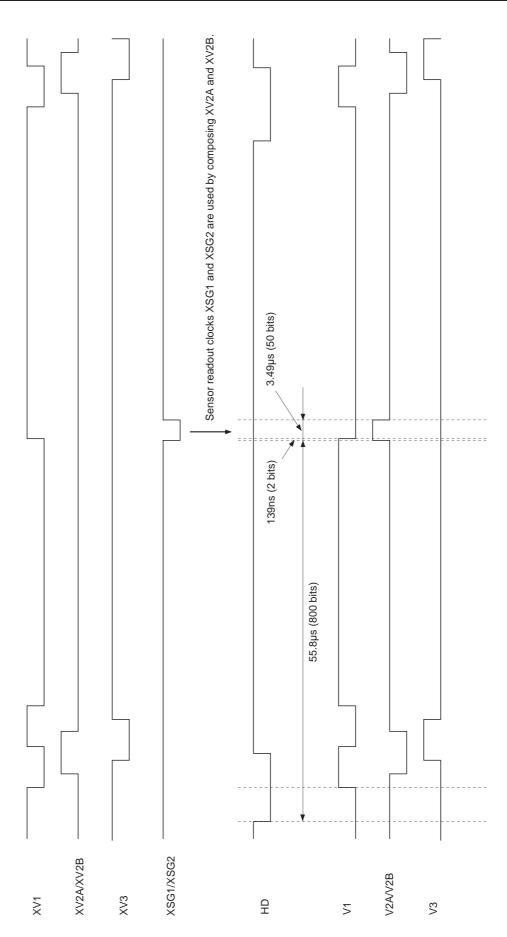
Lag = (Vlag/150) × 100 [%]

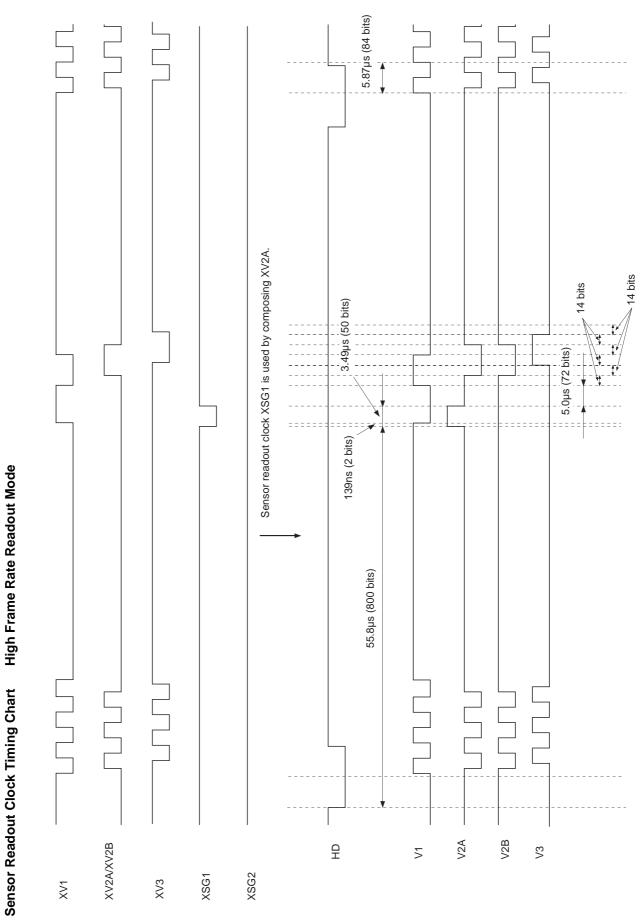




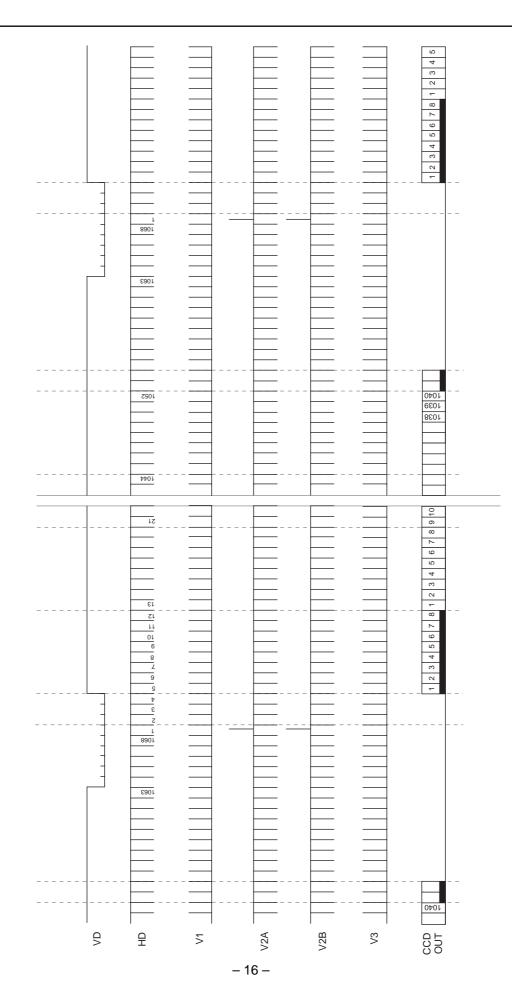
**Drive Circuit** 

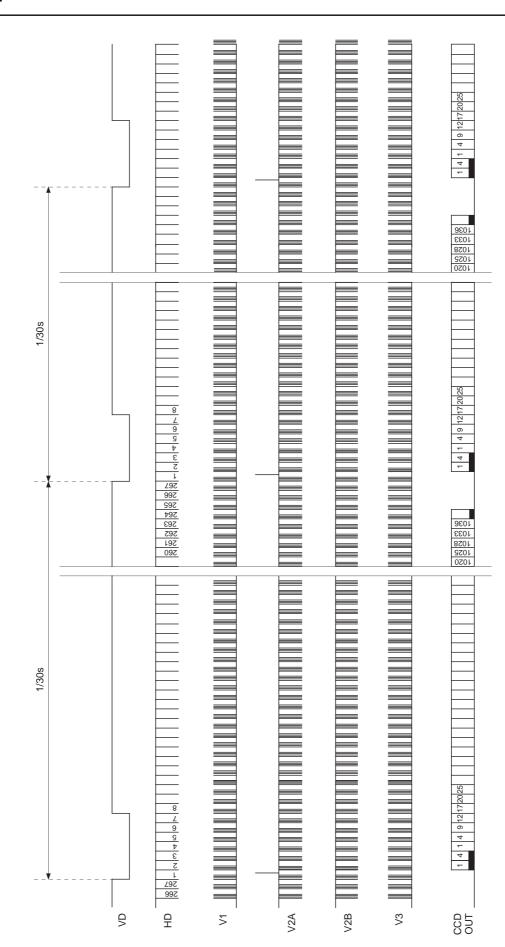
Sensor Readout Clock Timing Chart Progressive Scan Mode

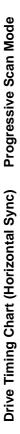


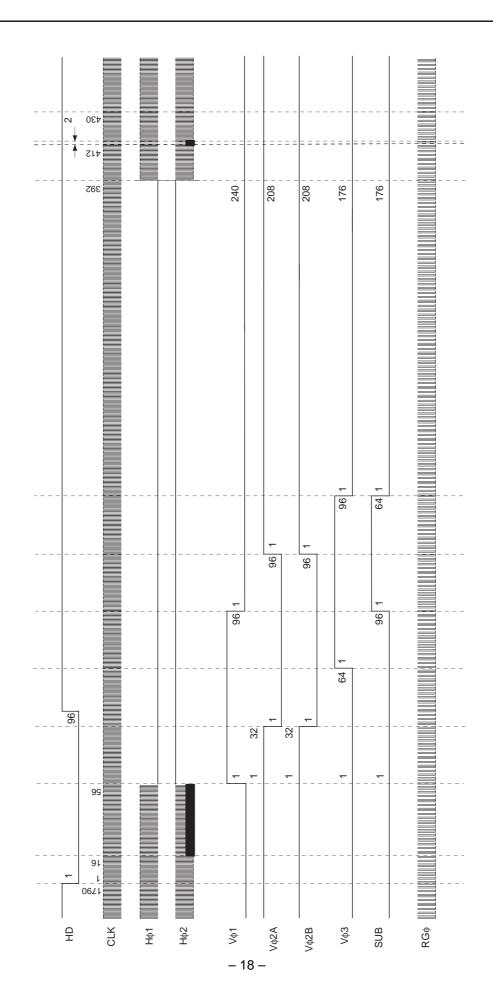


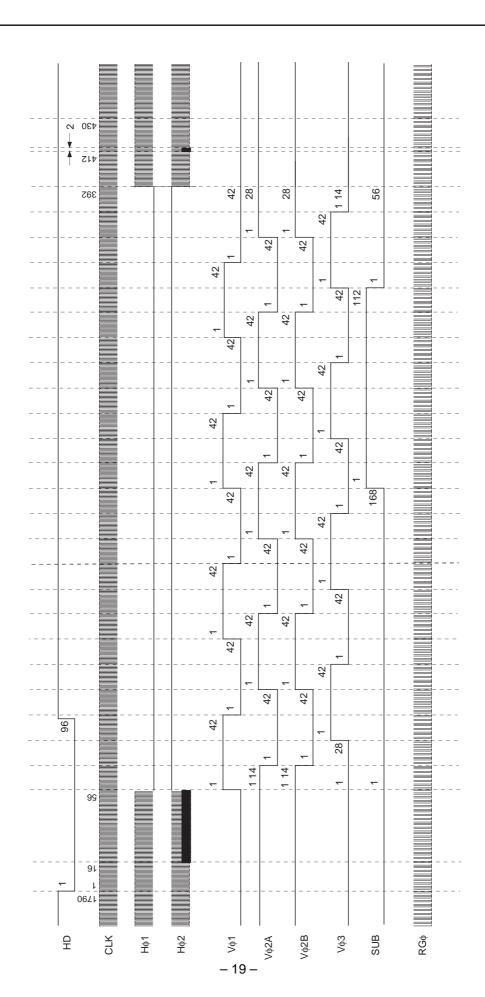
ICX205AL











### Notes on Handling

1) Static charge prevention

CCD image sensors are easily damaged by static discharge. Before handling be sure to take the following protective measures.

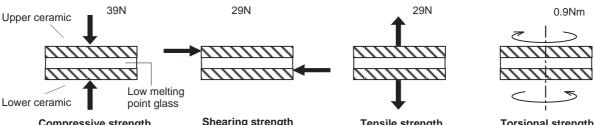
a) Either handle bare handed or use non-chargeable gloves, clothes or material.

Also use conductive shoes.

- b) When handling directly use an earth band.
- c) Install a conductive mat on the floor or working table to prevent the generation of static electricity.
- d) lonized air is recommended for discharge when handling CCD image sensor.
- e) For the shipment of mounted substrates, use boxes treated for the prevention of static charges.
- 2) Soldering
  - a) Make sure the package temperature does not exceed 80°C.
  - b) Solder dipping in a mounting furnace causes damage to the glass and other defects. Use a ground 30W soldering iron and solder each pin in less than 2 seconds. For repairs and remount, cool sufficiently.
  - c) To dismount an image sensor, do not use a solder suction equipment. When using an electric desoldering tool, use a thermal controller of the zero cross On/Off type and connect it to ground.
- 3) Dust and dirt protection

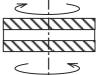
Image sensors are packed and delivered by taking care of protecting its glass plates from harmful dust and dirt. Clean glass plates with the following operation as required, and use them.

- a) Perform all assembly operations in a clean room (class 1000 or less).
- b) Do not either touch glass plates by hand or have any object come in contact with glass surfaces. Should dirt stick to a glass surface, blow it off with an air blower. (For dirt stuck through static electricity ionized air is recommended.)
- c) Clean with a cotton bud and ethyl alcohol if the grease stained. Be careful not to scratch the glass.
- d) Keep in a case to protect from dust and dirt. To prevent dew condensation, preheat or precool when moving to a room with great temperature differences.
- e) When a protective tape is applied before shipping, just before use remove the tape applied for electrostatic protection. Do not reuse the tape.
- 4) Installing (attaching)
  - a) Remain within the following limits when applying a static load to the package. Do not apply any load more than 0.7mm inside the outer perimeter of the glass portion, and do not apply any load or impact to limited portions. (This may cause cracks in the package.)



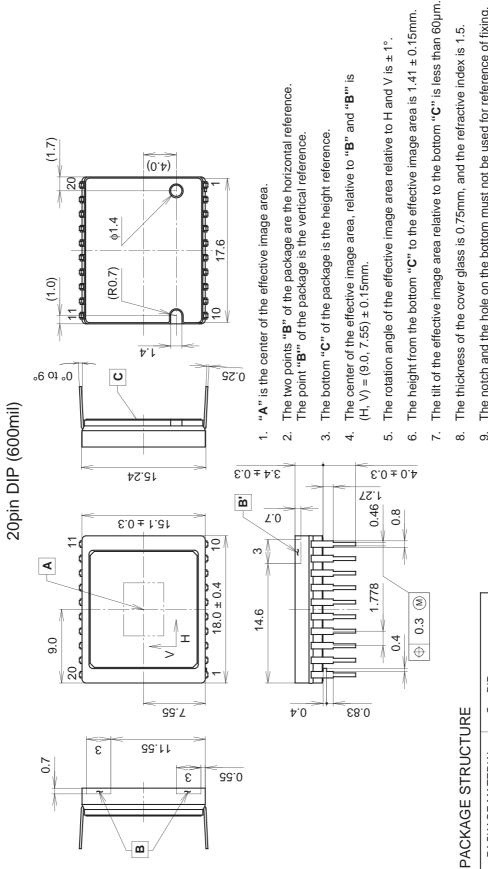
Shearing strength

**Tensile strength** 



Torsional strength

- b) If a load is applied to the entire surface by a hard component, bending stress may be generated and the package may fracture, etc., depending on the flatness of the ceramic portions. Therefore, for installation, use either an elastic load, such as a spring plate, or an adhesive.
- c) The adhesive may cause the marking on the rear surface to disappear, especially in case the regulated voltage value is indicated on the rear surface. Therefore, the adhesive should not be applied to this area, and indicated values should be transferred to other locations as a precaution.
- d) The upper and lower ceramic are joined by low melting point glass. Therefore, care should be taken not to perform the following actions as this may cause cracks.
  - Applying repeated bending stress to the outer leads.
  - Heating the outer leads for an extended period with a soldering iron.
  - Rapidly cooling or heating the package.
  - Applying any load or impact to a limited portion of the low melting point glass using tweezers or other sharp tools.
  - Prying at the upper or lower ceramic using the low melting point glass as a fulcrum.
  - Note that the same cautions also apply when removing soldered products from boards.
- e) Acrylate anaerobic adhesives are generally used to attach CCD image sensors. In addition, cyanoacrylate instantaneous adhesives are sometimes used jointly with acrylate anaerobic adhesives. (reference)
- 5) Others
  - a) Do not expose to strong light (sun rays) for long periods. For continuous using under cruel condition exceeding the normal using condition, consult our company.
  - b) Exposure to high temperature or humidity will affect the characteristics. Accordingly avoid storage or usage in such conditions.



Cer-DIP	TIN PLATING	42 ALLOY	2.6g	
PACKAGE MATERIAL	LEAD TREATMENT	LEAD MATERIAL	PACKAGE WEIGHT	

- The notch and the hole on the bottom must not be used for reference of fixing. *б*

۵